

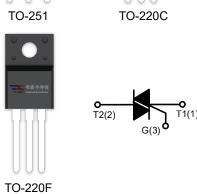
### **DESCRIPTION:**

The BT138X-600F SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.



#### **MAIN FEATURES**

Symbol	Value	Unit
I <sub>T(RMS)</sub>	12	Α
V <sub>DRM</sub> /V <sub>RRM</sub>	600/800	V



## **ABSOLUTE MAXIMUM RATINGS**

Parameter		Symbol	Value	Unit
Storage junction temperature range		T <sub>stg</sub>	-40-150	$^{\circ}$
Operating junction tem	perature range	Tj	-40-125	$^{\circ}$
Repetitive peak off-state voltage(T <sub>j</sub> =25℃)		V <sub>DRM</sub>	600/800	V
Repetitive peak reverse voltage(T <sub>j</sub> =25℃)		V <sub>RRM</sub>	600/800	V
Non repetitive surge peak Off-state voltage		V <sub>DSM</sub>	V <sub>DRM</sub> + 100	V
Non repetitive peak reverse voltage		V <sub>RSM</sub>	V <sub>RRM</sub> + 100	V
RMS on-state current	TO-251/ TO-220C(T <sub>C</sub> =95°C) TO-220F(Ins) (T <sub>C</sub> =80°C)	- I <sub>T(RMS)</sub>	12	А
Non repetitive surge peak on-state current (full cycle, F=50Hz)		Ітѕм	95	А
I <sup>2</sup> t value for fusing (tp=10ms)		l <sup>2</sup> t	45	A <sup>2</sup> s



Critical rate of rise of on-state	I - II -III	- dl/dt	50	A/µs
current(I <sub>G</sub> =2×I <sub>GT</sub> )	IV		10	
Peak gate current		I <sub>GM</sub>	2	Α
Average gate power dissipation		P <sub>G(AV)</sub>	0.5	W
Peak gate power		P <sub>GM</sub>	5	W

# **ELECTRICAL CHARACTERISTICS** (T<sub>j</sub>=25 °C unless otherwise specified)

Symbol	Test Condition	Quadrant			Value		Hoit
Symbol	rest Condition			D	E	F	Unit
	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	I - II -III	MAX	5	10	25	mA
I <sub>GT</sub>		IV		10	25	70	
V <sub>G</sub> T		ALL	MAX		1.5		V
V <sub>GD</sub>	$V_D=V_{DRM}T_j=125$ °C RL=3.3KΩ	ALL	MIN	0.2		V	
IL	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III	MAX	15	30	40	mA
		II - IV		20	40	80	
Ін	I <sub>T</sub> =100mA		MAX	10	25	30	mA
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125℃		MIN	20	50	50	V/µs

### **STATIC CHARACTERISTICS**

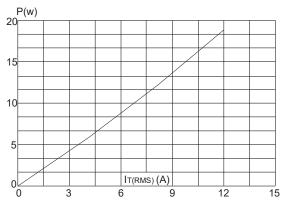
Symbol	Parameter		Value(MAX)	Unit
V <sub>TM</sub>	I <sub>TM</sub> =15A tp=380µs	Tj=25℃	1.6	V
IDRM	- V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	Tj=25℃	5	μA
I <sub>RRM</sub>		Tj=125℃	1	mA

### **THERMAL RESISTANCES**

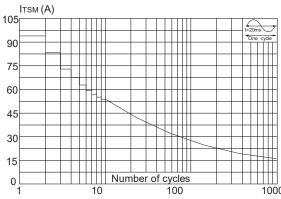
Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	junction to case(AC)	TO-220C	1.4	°C/W
		TO-220F(Ins)	2.5	
		TO-251	1.7	



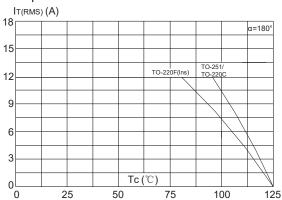
**FIG.1:** Maximum power dissipation versus RMS on-state current



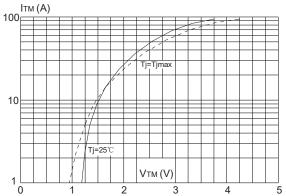
**FIG.3:** Surge peak on-state current versus number of cycles



**FIG.2:** RMS on-state current versus case temperature



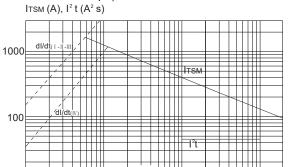
**FIG.4:** On-state characteristics (maximum values)





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**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of  $I^2t(I-II-III:dI/dt < 50A/\mu s; IV:dI/dt < 10A/\mu s)$ 



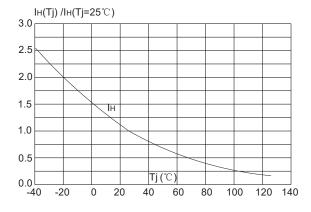
**FIG.7:** Relative variations of holding current versus junction temperature

tp(ms)

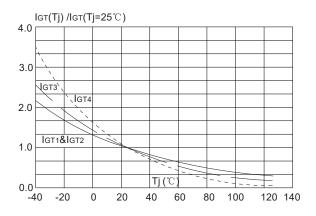
1

10 20

0.1



**FIG.6:** Relative variations of gate trigger current versus junction temperature



**FIG.8:** Relative variations of latching current versus junction temperature

